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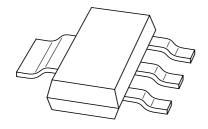
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PZTA42NPN high-voltage transistor

Product data sheet Supersedes data of 1997 Jun 16 1999 May 21



NPN high-voltage transistor

PZTA42

FEATURES

• Low current (max. 100 mA)

• High voltage (max. 300 V).

APPLICATIONS

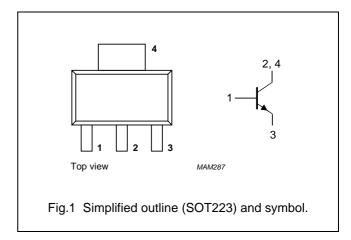
• Telephony and professional communication equipment.

DESCRIPTION

NPN high-voltage transistor in a SOT223 plastic package. PNP complement: PZTA92.

PINNING

PIN	DESCRIPTION
1	base
2,4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	300	V
V_{CEO}	collector-emitter voltage	open base	-	300	V
V_{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	1.2	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

NPN high-voltage transistor

PZTA42

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	104	K/W
R _{th j-s}	thermal resistance from junction to soldering point		23	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 200 V	_	20	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{BE} = 6 V	_	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V			
		I _C = 1 mA	25	_	
		I _C = 10 mA	40	_	
		I _C = 30 mA	40	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	_	500	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	_	900	mV
C _{re}	feedback capacitance	I _C = i _c = 0; V _{CB} = 20 V; f = 1 MHz	_	3	pF
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 20 \text{ V}; f = 100 \text{ MHz}$	50	_	MHz

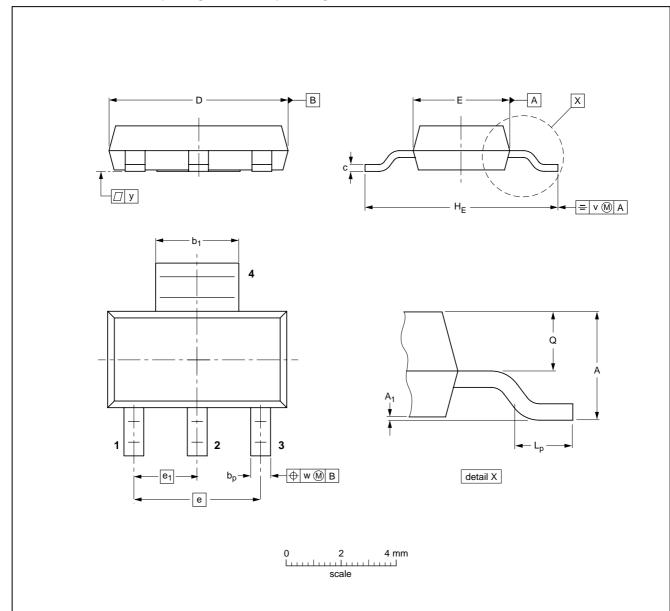
NPN high-voltage transistor

PZTA42

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	bp	b ₁	С	D	E	е	e ₁	HE	Lp	Q	٧	w	у
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE				
VERSION			IEC JEDEC EIAJ			PROJECTION	ISSUE DATE	
SOT223			SC-73		$ \ \ \bigoplus \big($	97-02-28 99-09-13		

NPN high-voltage transistor

PZTA42

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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